R1LP0408D Series

4Mb Advanced LPSRAM (512-kword × 8-bit)

R10DS0274EJ0200
Rev.2.00
2019.10.29

Description

The R1LP0408D Series is a family of 4-Mbit static RAMs organized 512-kword × 8-bit, fabricated by Renesas's high-performance CMOS and TFT technologies. The R1LP0408D Series has realized higher density, higher performance and low power consumption. The R1LP0408D Series offers low power standby power dissipation; therefore, it is suitable for battery backup systems. It is offered in 32-pin SOP and 32-pin TSOP.

Features

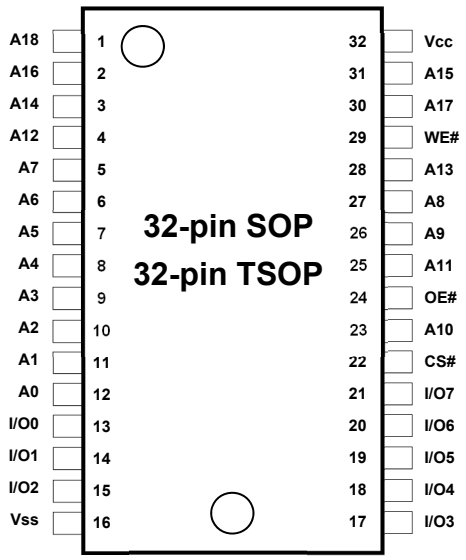
- Single 5V supply: 4.5V to 5.5V
- Access time: 55ns (max.)
- Power dissipation:
  — Standby: 4µW (typ.)
- Equal access and cycle times
- Common data input and output
  — Three state output
- Directly TTL compatible
  — All inputs and outputs
- Battery backup operation

Ordering Information

Orderable part name	Access time	Temperature range	Package	Shipping container
R1LP0408DSP-5SI#B*	55 ns	-40 ~ +85°C	525-mil 32-pin plastic SOP	Tube (Magazine)
R1LP0408DSP-5SI#S*				Embossed tape
R1LP0408DSB-5SI#B*			400-mil 32-pin plastic TSOP (II)	Tray
R1LP0408DSB-5SI#S*				Embossed tape

Note 1. * = Revision code for Assembly site change, etc. (* = 0, 1, etc.)

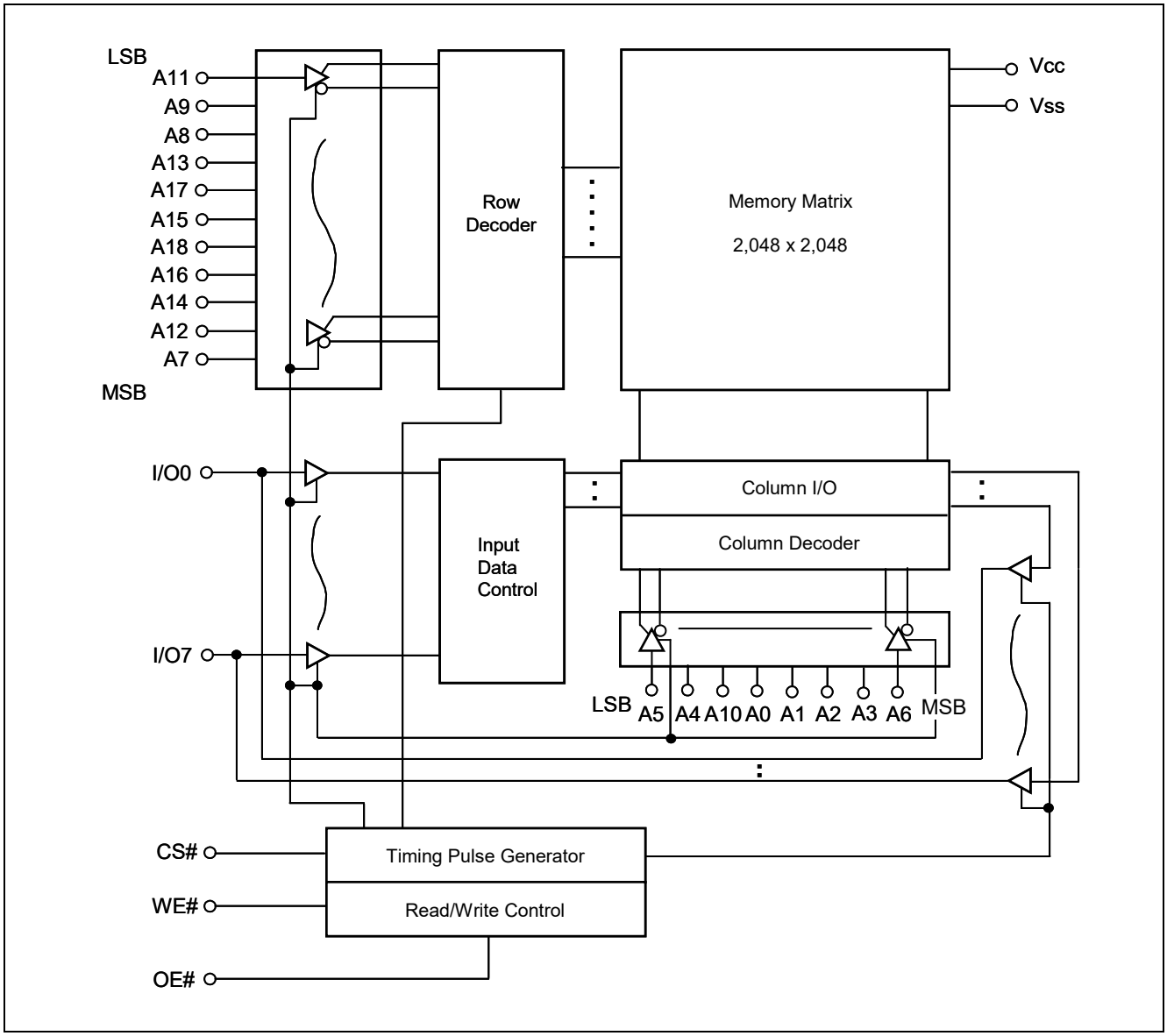
Pin Arrangement



Pin Description

Pin name	Function
Vcc	Power supply
Vss	Ground
A0 to A18	Address input
I/O0 to I/O7	Data input/output
CS#	Chip select
WE#	Write enable
OE#	Output enable

Block Diagram



Operation Table

WE#	CS#	OE#	Mode	Vcc current	I/O0 to I/O7	Ref. cycle
×	H	×	Not selected	I_{SB}, I_{SB1}	High-Z	—
H	L	H	Output disable	Icc	High-Z	—
H	L	L	Read	Icc	Dout	Read cycle
L	L	H	Write	Icc	Din	Write cycle (1)
L	L	L	Write	Icc	Din	Write cycle (2)

Note 1. H: V_{IH} L:V_{IL} ×: V_{IH} or V_{IL}

Absolute Maximum Ratings

Parameter	Symbol	Value	unit
Power supply voltage relative to Vss	Vcc	-0.5 to +7.0	V
Terminal voltage on any pin relative to Vss	V_T	-0.5[*1] to Vcc+0.3[*2]	V
Power dissipation	P_T	0.7	W
Operation temperature	Topr	-40 to +85	°C
Storage temperature range	Tstg	-65 to 150	°C
Storage temperature range under bias	Tbias	-40 to +85	°C

Note 1. -3.0V for pulse ≤ 30ns (full width at half maximum)
2. Maximum voltage is +7.0V.

DC Operating Conditions

Parameter	Symbol	Min.	Typ.	Max.	Unit	Note
Supply voltage	Vcc	4.5	5.0	5.5	V	
	Vss	0	0	0	V	
Input high voltage	V_{IH}	2.2	—	Vcc+0.3	V	
Input low voltage	V_{IL}	-0.3	—	0.8	V	1
Ambient temperature range	Ta	-40	—	+85	°C	

Note 1. -3.0V for pulse ≤ 30ns (full width at half maximum)

DC Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions
Input leakage current	$\lvert I_{LI} \rvert$	—	—	1	µA	Vin = Vss to Vcc
Output leakage current	$\lvert I_{LO} \rvert$	—	—	1	µA	CS# =V_{IH} or OE# =V_{IH}, VI/O =Vss to Vcc
Operating current	Icc	—	5*1	10	mA	CS# =V_{IL}, Others = V_{IH}/V_{IL}, II/O = 0mA
Average operating current	I_{CC1}	—	15*1	25	mA	Min. cycle, duty =100%, II/O = 0mA, CS# =V_{IL}, Others = V_{IH}/V_{IL}
	I_{CC2}	—	3*1	5	mA	Cycle =1µs, duty =100%, II/O = 0mA, CS# ≤ 0.2V, V_{IH} ≥ Vcc-0.2V, V_{IL} ≤ 0.2V
Standby current	I_{SB}	—	0.1*1	0.5	mA	CS# =V_{IH}, Others = Vss to Vcc
Standby current	I_{SB1}	—	0.8*1	2.5	µA	~+25°C; Vin = Vss to Vcc, CS# ≥ Vcc-0.2V
		—	1*2	3	µA	~+40°C
		—	—	8	µA	~+70°C
		—	—	10	µA	~+85°C
Output high voltage	V_{OH}	2.4	—	—	V	I_{OH} = -1mA
	V_{OH2}	Vcc-0.5	—	—	V	I_{OH} = -0.1mA
Output low voltage	V_{OL}	—	—	0.4	V	I_{OL} = 2.1mA

Note 1. Typical parameter indicates the value for the center of distribution at 5.0V (Ta=25ºC), and not 100% tested.
2. Typical parameter indicates the value for the center of distribution at 5.0V (Ta=40ºC), and not 100% tested.

Capacitance

(Vcc = 4.5V ~ 5.5V, f = 1MHz, Ta = -40 ~ +85°C)

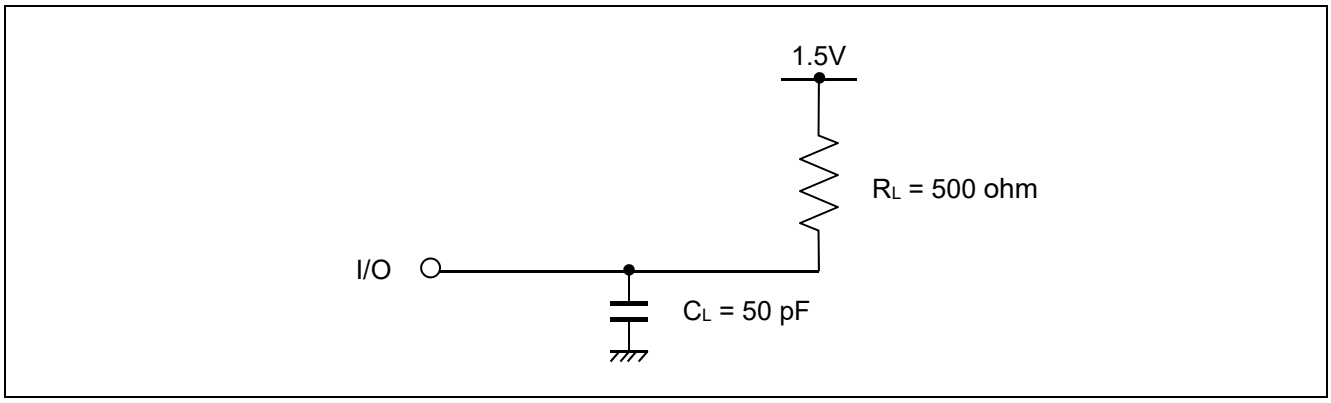
Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions	Note
Input capacitance	C in	—	—	8	pF	Vin =0V	1
Input / output capacitance	$C_{I/O}$	—	—	10	pF	VI/O =0V	1

Note 1. This parameter is sampled and not 100% tested.

AC Characteristics

Test Conditions (Vcc = 4.5V ~ 5.5V, Ta = -40 ~ +85°C)

- Input pulse levels: VIL = 0.4V, VIH = 2.4V
- Input rise and fall time: 5ns
- Input and output timing reference level: 1.5V
- Output load: See figures (Including scope and jig)



Read Cycle

Parameter	Symbol	Min.	Max.	Unit	Note
Read cycle time	t_{RC}	55	—	ns	
Address access time	t_{AA}	—	55	ns	
Chip select access time	t_{ACS}	—	55	ns	
Output enable to output valid	t_{OE}	—	25	ns	
Chip select to output in low-Z	t_{CLZ}	10	—	ns	2
Output enable to output in low-Z	t_{OLZ}	5	—	ns	2
Chip deselect to output in high-Z	t_{CHZ}	0	20	ns	1,2
Output disable to output in high-Z	t_{OHZ}	0	20	ns	1,2
Output hold from address change	t_{OH}	10	—	ns	

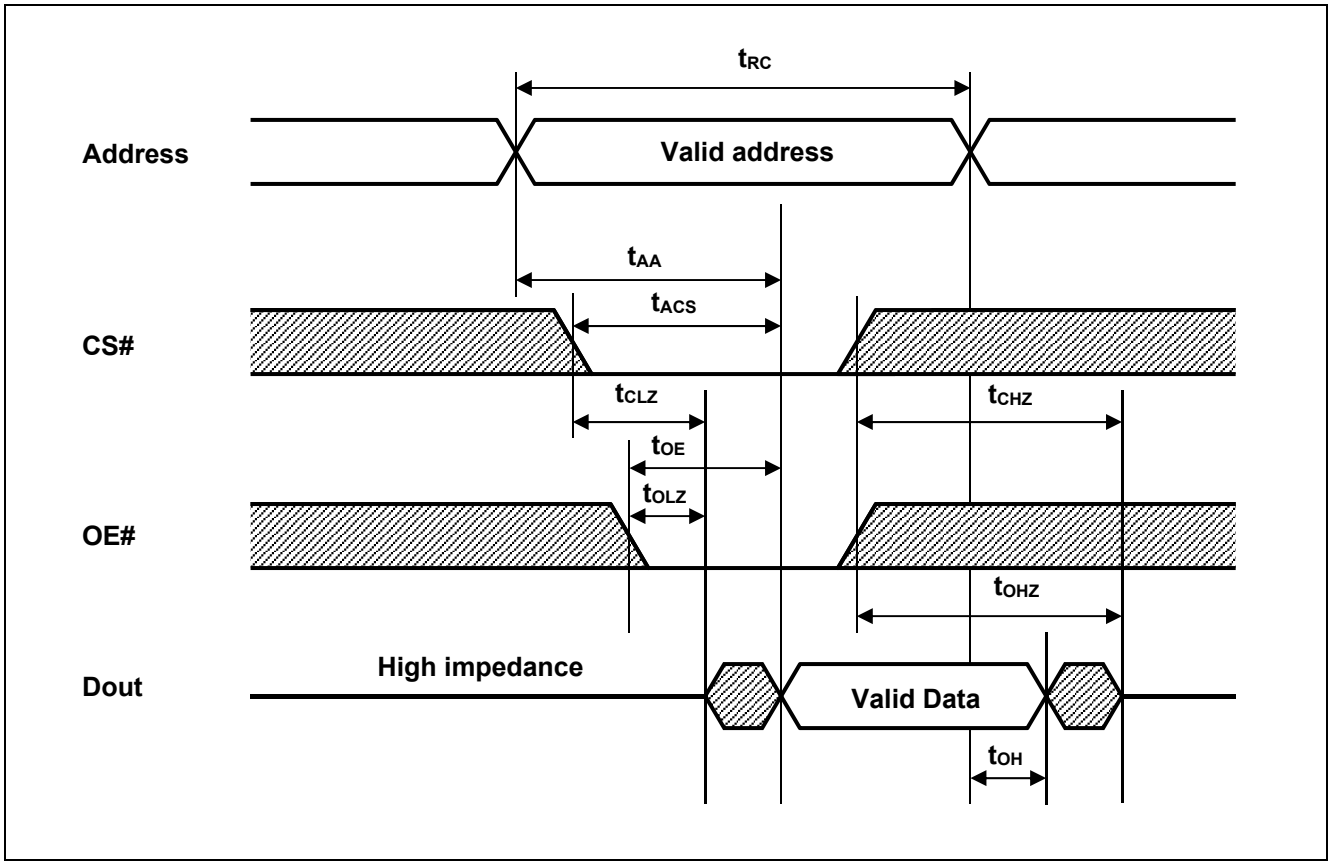
Write Cycle

Parameter	Symbol	Min.	Max.	Unit	Note
Write cycle time	t_{WC}	55	—	ns	
Chip select to end of write	t_{CW}	50	—	ns	4
Address setup time	t_{AS}	0	—	ns	5
Address valid to end of write	t_{AW}	50	—	ns	
Write pulse width	t_{WP}	40	—	ns	3,12
Write recovery time	t_{WR}	0	—	ns	6
Write to output in high-Z	t_{WHZ}	0	20	ns	1,2,7
Data to write time overlap	t_{DW}	25	—	ns	
Data hold from write time	t_{DH}	0	—	ns	
Output enable from end of write	t_{OW}	5	—	ns	2
Output disable to output in high-Z	t_{OHZ}	0	20	ns	1,2,7

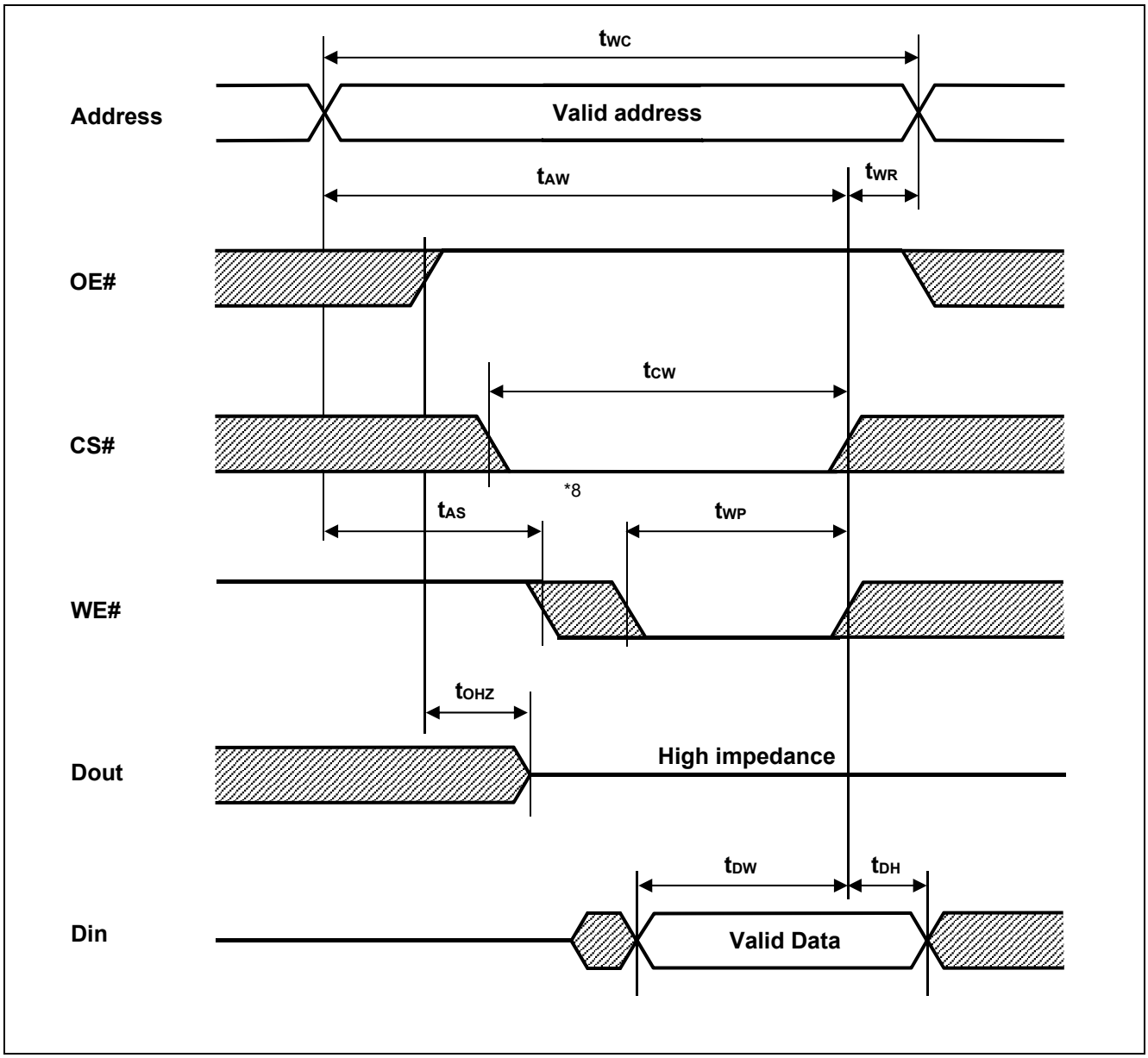
Note
1. t_{CHZ}, t_{OHZ} and t_{WHZ} are defined as the time at which the outputs achieve the open circuit conditions and are not referred to output voltage levels.
2. This parameter is sampled and not 100% tested.
3. A write occurs during the overlap (t_{WP}) of a low CS# and a low WE#.
   A write begins at the later transition of CS# going low or WE# going low.
   A write ends at the earlier transition of CS# going high or WE# going high.
   t_{WP} is measured from the beginning of write to the end of write.
4. t_{CW} is measured from CS# going low to end of write.
5. t_{AS} is measured the address valid to the beginning of write.
6. t_{WR} is measured from the earlier of WE# or CS# going high to the end of write cycle.
7. During this period, I/O pins are in the output state so that the input signals of the opposite phase to the outputs must not be applied.
8. If the CS# low transition occurs simultaneously with the WE# low transition or after the WE# transition, the output remain in a high impedance state.
9. Dout is the same phase of the write data of this write cycle.
10. Dout is the read data of next address.
11. If CS# is low during this period, I/O pins are in the output state. Therefore, the input signals of the opposite phase to the outputs must not be applied to them.
12. In the write cycle with OE# low fixed, t_{WP} must satisfy the following equation to avoid a problem of data bus contention.
    $t_{WP} \geq t_{DW}$ min + t_{WHZ} max

Timing Waveforms

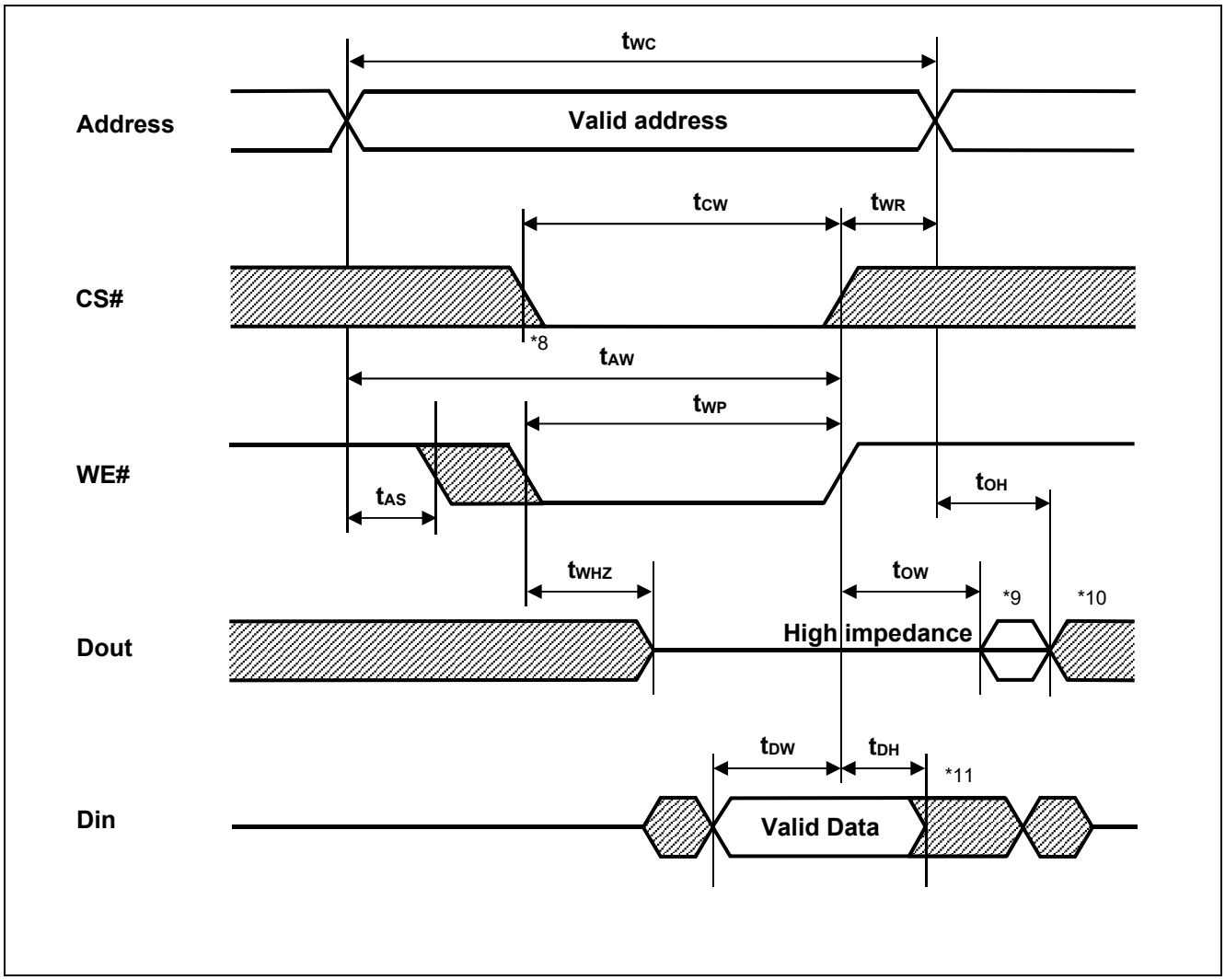
Read Cycle (WE# = V_{IH})



Write Cycle (1) (OE# CLOCK)



Write Cycle (2) (OE# Low Fixed)



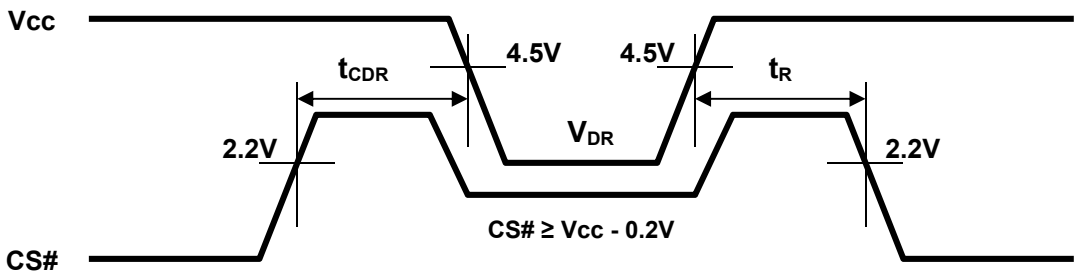
Low Vcc Data Retention Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions[*3]	
V_{CC} for data retention	V_{DR}	2.0	—	5.5	V	Vin ≥ 0V, CS# ≥ Vcc-0.2V	
Data retention current	I_{CCDR}	—	0.8[*1]	2.5	µA	~+25°C	Vcc=3.0V, Vin ≥ 0V, CS# ≥ Vcc-0.2V
		—	1[*2]	3	µA	~+40°C	
		—	—	8	µA	~+70°C	
		—	—	10	µA	~+85°C	
Chip deselect time to data retention	t_{CDR}	0	—	—	ns	See retention waveform.	
Operation recovery time	t_R	5	—	—	ms		

Note 1. Typical parameter indicates the value for the center of distribution at 3.0V (Ta=25ºC), and not 100% tested.
2. Typical parameter indicates the value for the center of distribution at 3.0V (Ta=40ºC), and not 100% tested.
3. CS# controls address buffer, WE# buffer, OE# buffer and Din buffer. If data retention mode, Vin levels (address, WE#, OE#, I/O) can be in the high impedance state.

Low Vcc Data Retention Timing Waveforms

CS# Controlled



Revision History	R1LP0408D Series Data Sheet

Rev.	Date	Description	
		Page	Summary
1.00	2017.1.27	—	First Edition issued
2.00	2019.10.29	p.1	Revised orderable part name information.

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Corporate Headquarters

TOYOSU FORESIA, 3-2-24 Toyosu,
Koto-ku, Tokyo 135-0061, Japan
www.renesas.com

Contact Information

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